ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE132
Silicon N–Channel JFET Transistor
VHF Amplifier, Mixer

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Drain–Gate Voltage, V_{DG} 25V

Gate–Source Voltage, V_{GS} . . . . . –25V

Gate Current, I_G 10mA

Total Device Dissipation (T_A = 25°C), P_D 200mW

Derate Above 25°C . . . . . 2mW/°C

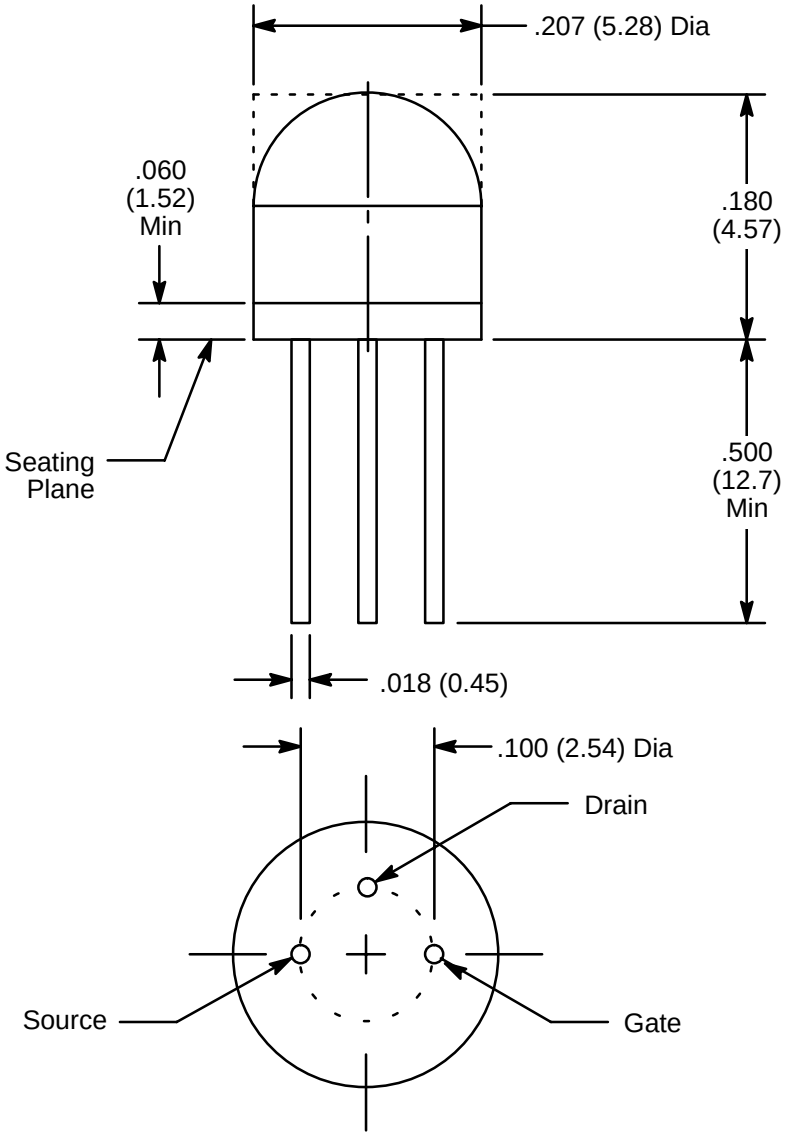
Operating Junction Temperature Range, T_J . . . . . –55° to +150°C

Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Lead Temperature (During Soldering, 1/16” from case for 10sec), T_L . . . . . +260°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate–Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = 1μA, V_{DS} = 0	–25	–	–	V
Gate Reverse Current	I_{GSS}	V_{GS} = 15V, V_{DS} = 0	–	–	–2	nA
		V_{GS} = 15V, V_{DS} = 0, T_A = +100°C	–	–	–2	nA
Gate–Source Cutoff Voltage	$V_{GS(off)}$	I_D = 2nA, V_{DS} = 15V	–	–	–8	V
Gate–Source Voltage	V_{GS}	I_D = 50μA, V_{DS} = 15V	–0.5	–	–7.5	V
Zero–Gate–Voltage Drain Current	I_{DSS}	V_{DS} = 15V, V_{GS} = 0	2	–	20	mA
Forward Transconductance	g_{fs}	V_{DS} = 15V, V_{GS} = 0, f = 1kHz	2500	–	7000	μmho
Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = 15V, V_{GS} = 0, f = 100MHz	2000	–	–	μmho
Output Admittance	$\|y_{os}\|$	V_{DS} = 15V, V_{GS} = 0, f = 1kHz	–	–	50	μmho


.207 (5.28) Dia
.060
(1.52)
Min
.180
(4.57)
Seating
Plane
.500
(12.7)
Min
.018 (0.45)
.100 (2.54) Dia
Drain
Source
Gate